



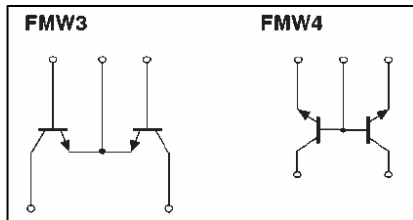
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-5L Plastic-Encapsulate Transistors

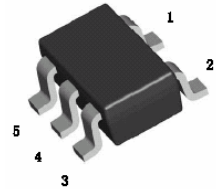
FMW3,FMW4 DUAL TRANSISTOR

FEATURES

High breakdown voltage



SOT-23-5L



MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector- Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Power Dissipation	0.3	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

MARKING: FMW3:W3 FMW4:W4

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}$, $I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=100\text{V}$, $I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}$, $I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}$, $I_C=2\text{mA}$	180		820	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$			0.5	V
Transition frequency	f_T	$V_{CE}=12\text{V}$, $I_C=2\text{mA}$, $f=100\text{MHz}$		140		MHz

Typical Characteristics

FMW3 FMW4

